

4. (Amended) The LPCVD apparatus according to claim 1, wherein said apparatus is provided with a trap-pressure-regulating valve for adjusting the internal pressure in the trap, and the exhaust pump.

5. (Amended) The LPCVD apparatus according to claim 1, whwerin said apparatus is provided with a back-flow valve for preventing a back flow of the used raw material in the trap, said back-flow valve being located between the reactor and the trap.

6. (Amended) The LPCVD apparatus according to claim 1, wherein said apparatus is connected with a first and a second pipes and provided with a by-pass pipe which bypasses the trap, said first pipe connecting the reactor and the trap and said second pipe connecting the trap and the pump.

7. (Amended) The LPCVD apparatus according to claim 1, wherein said by-pass pipe is provided at the both ends thereof with a back-flow valve.

8. (Amended) A method of manufacturing a thin film with the use of the LPCVD apparatus, said apparatus defined in claim 1, wherein an internal pressure in the trap is kept equal to or lower than that in the reactor.

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